

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	30 A
V_{RRM}	45 V
T_j (max)	175°C
V_F (max)	0.63 V

FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW THERMAL RESISTANCE
- HIGH DISSIPATION MINIATURE PACKAGE

DESCRIPTION

Single Schottky rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged in D²PAK surface mount package , this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	45	V
I _{F(RMS)}	RMS forward current	50	A
I _{F(AV)}	Average forward current	30	A
I _{FSM}	Surge non repetitive forward current	200	A
I _{RRM}	Repetitive peak reverse current	1	A
I _{RSR}	Non Repetitive peak reverse current	3	A
T _{stg}	Storage temperature range	- 65 to + 175	°C
T _j	Maximum operating junction temperature*	175	°C
dV/dt	Critical rate of rise of reverse voltage	10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

STPS3045G

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th} (j-c)	Junction to case	1	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			500	µA
		T _j = 125°C			20	80	mA
V _F **	Forward voltage drop	T _j = 125°C	I _F = 30 A		0.53	0.63	V
		T _j = 25°C	I _F = 60 A			0.84	
		T _j = 125°C	I _F = 60 A		0.68	0.78	

Pulse test : * tp = 5 ms, δ < 2 %
** tp = 380 µs, δ < 2%

To evaluate the conduction losses use the following equation:
P = 0.48 x I_{F(av)} + 0.005 I_F² (RMS)

Fig. 1: Average forward power dissipation versus average forward current.

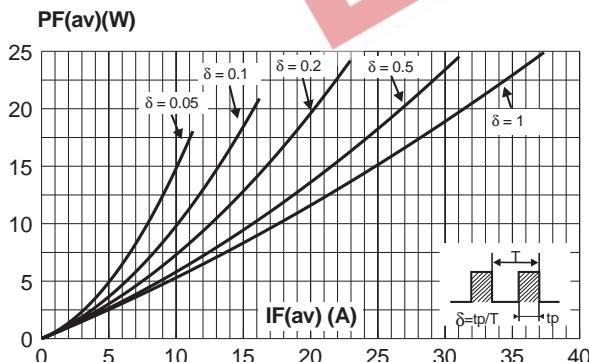


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

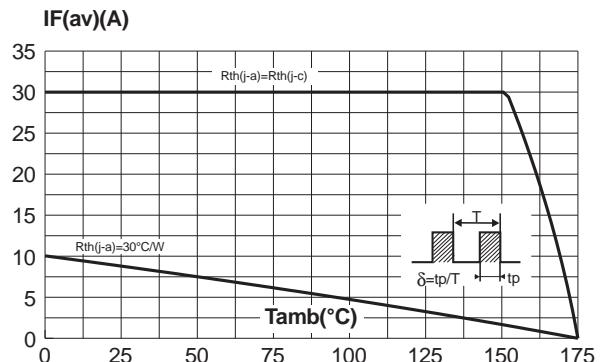


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values).

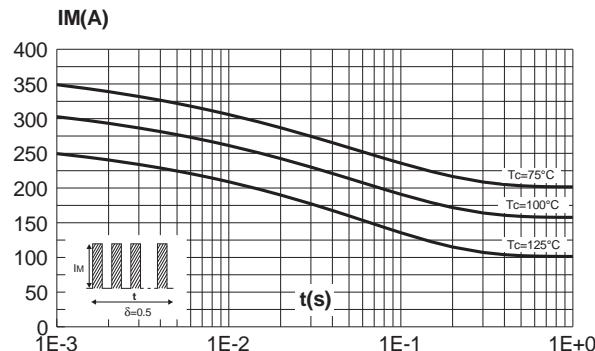


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values)

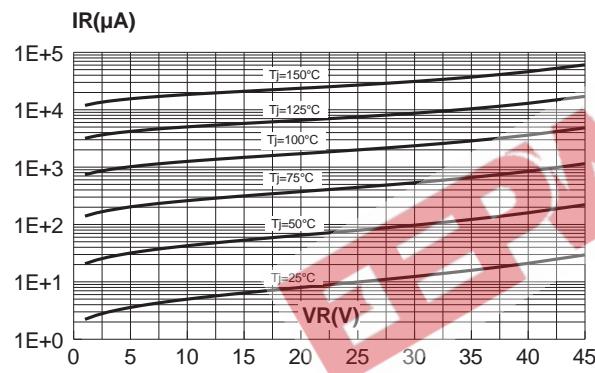


Fig. 7: Forward voltage drop versus forward current (maximum values).

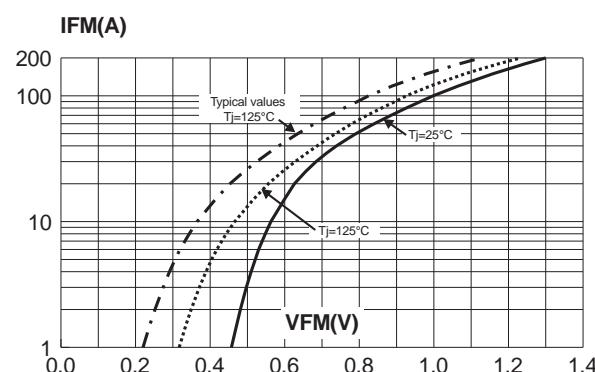


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration.

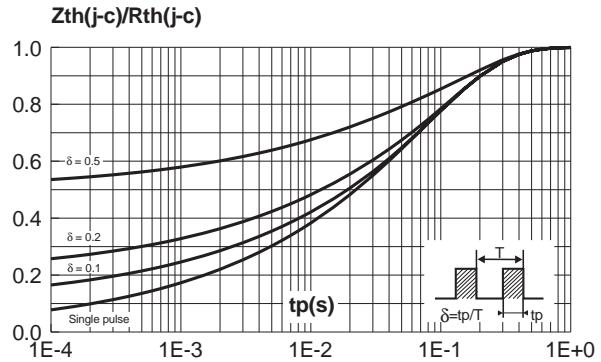


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).

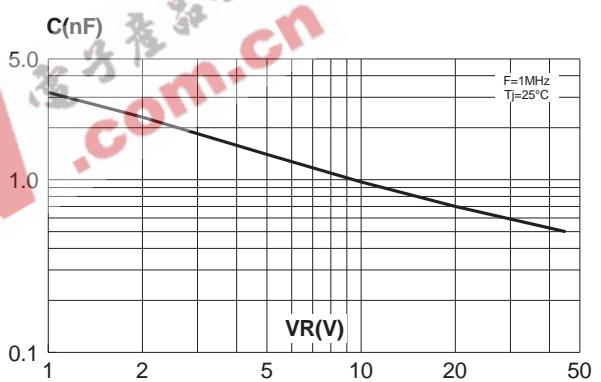
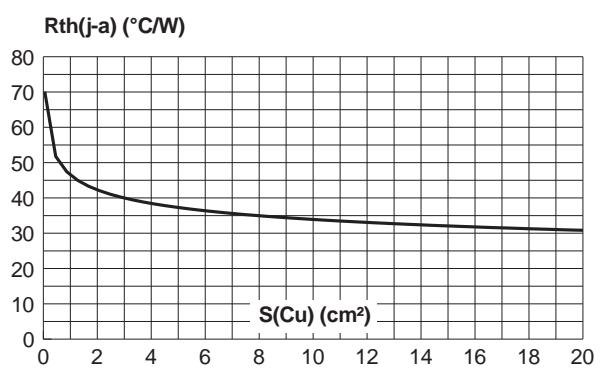
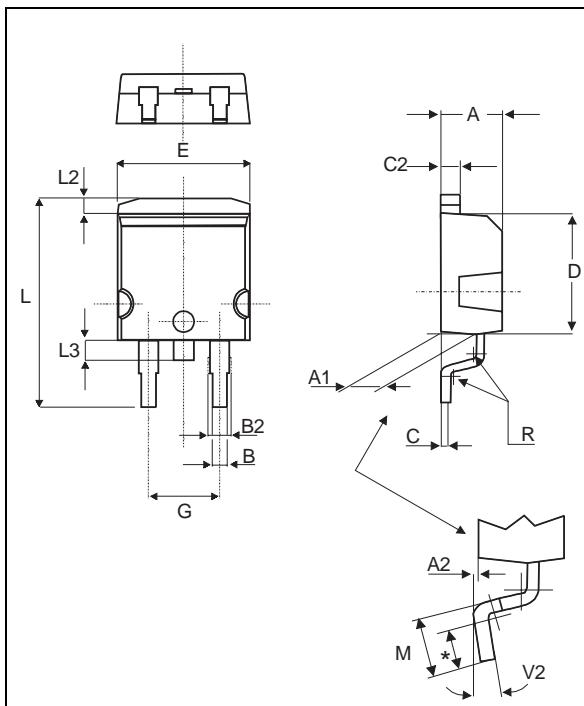


Fig. 8: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board, copper thickness: $35\mu\text{m}$)



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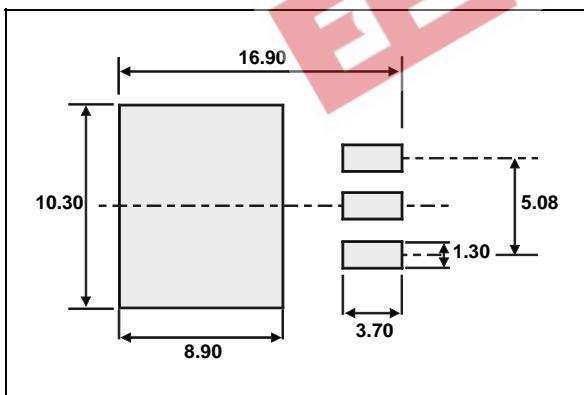
PACKAGE MECHANICAL DATA D²PAK



* FLAT ZONE NO LESS THAN 2mm

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

FOOTPRINT DIMENSIONS (in millimeters)



Type	Marking	Package	Weight	Base qty	Delivery mode
STPS3045G	STPS3045G	D ² PAK	1.48g	50	Tube
STPS3045G-TR	STPS3045G	D ² PAK	1.48g	500	Tape & Reel

- Epoxy meets UL94, V0

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